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ABSTRACT OF THE DISCLOSURE

An inexpensive and small-sized semiconductor device with high output performance is provided. The 5 semiconductor device comprises a semiconductor substrate; an active region formed on the semiconductor substrate; first and second channel regions formed on the active region so that the directions of the widths of both channel regions are substantially perpendicular to each other; bent 10 gate electrodes formed on the first and second channel regions; and source electrodes and drain electrodes formed with the gate electrodes therebetween, respectively.

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